

SEMiX703GB126HDs



SEMiX® 3s

Trench IGBT Modules

SEMiX703GB126HDs

Features

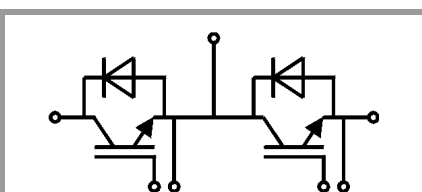
- Homogeneous Si
- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability
- UL recognised file no. E63532

Typical Applications*

- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.
- Not for new design



GB

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
IGBT				
V _{CES}	T _j = 25 °C		1200	V
I _C	T _j = 150 °C	T _c = 25 °C	642	A
		T _c = 80 °C	449	A
I _{Cnom}			450	A
I _{CRM}	I _{CRM} = 2xI _{Cnom}		900	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 600 V V _{GE} ≤ 20 V V _{CES} ≤ 1200 V	T _j = 125 °C	10	μs
T _j			-40 ... 150	°C
Inverse diode				
I _F	T _j = 150 °C	T _c = 25 °C	561	A
		T _c = 80 °C	384	A
I _{Fnom}			450	A
I _{FRM}	I _{FRM} = 2xI _{Fnom}		900	A
I _{FSM}	t _p = 10 ms, sin 180°, T _j = 25 °C		2900	A
T _j			-40 ... 150	°C
Module				
I _{t(RMS)}	T _{terminal} = 80 °C		600	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC sinus 50Hz, t = 1 min		4000	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
IGBT						
V _{CE(sat)}	I _C = 450 A	T _j = 25 °C		1.7	2.10	V
	V _{GE} = 15 V chipelevel	T _j = 125 °C		2.0	2.45	V
V _{CE0}	chipelevel	T _j = 25 °C		1	1.2	V
		T _j = 125 °C		0.9	1.1	V
r _{CE}	V _{GE} = 15 V chipelevel	T _j = 25 °C		1.6	2.0	mΩ
		T _j = 125 °C		2.4	3.0	mΩ
V _{GE(th)}	V _{GE} =V _{CE} , I _C = 18 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V	T _j = 25 °C				mA
	V _{CE} = 1200 V	T _j = 125 °C				mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz	32.3			nF
C _{oes}		f = 1 MHz	1.69			nF
C _{res}		f = 1 MHz	1.46			nF
Q _G	V _{GE} = - 8 V...+ 15 V		3600			nC
R _{Gint}	T _j = 25 °C		1.67			Ω
t _{d(on)}	V _{CC} = 600 V	T _j = 125 °C	310			ns
t _r	I _C = 450 A	T _j = 125 °C	60			ns
E _{on}	V _{GE} = ±15 V	T _j = 125 °C	32			mJ
t _{d(off)}	R _{G on} = 1.6 Ω	T _j = 125 °C	680			ns
t _f	R _{G off} = 1.6 Ω	T _j = 125 °C	135			ns
E _{off}		T _j = 125 °C	68			mJ
R _{th(j-c)}	per IGBT		0.061			K/W

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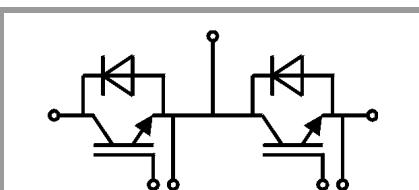
- AC inverter drives
- UPS
- Electronic Welding

Remarks

- Case temperatur limited to $T_C=125^\circ\text{C}$ max.
- Not for new design

Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverse diode						
$V_F = V_{EC}$	$I_F = 450\text{ A}$	$T_j = 25^\circ\text{C}$		1.6	1.80	V
	$V_{GE} = 0\text{ V}$	$T_j = 125^\circ\text{C}$		1.6	1.8	V
V_{F0}	chiplevel	$T_j = 25^\circ\text{C}$	0.9	1	1.1	V
		$T_j = 125^\circ\text{C}$	0.7	0.8	0.9	V
r_F	chiplevel	$T_j = 25^\circ\text{C}$	1.1	1.3	1.6	m Ω
		$T_j = 125^\circ\text{C}$	1.6	1.8	2.0	m Ω
I_{RRM}	$I_F = 450\text{ A}$	$T_j = 125^\circ\text{C}$		580		A
Q_{rr}	$di/dt_{off} = 8500\text{ A}/\mu\text{s}$	$T_j = 125^\circ\text{C}$		130		μC
E_{rr}	$V_{GE} = -15\text{ V}$	$T_j = 125^\circ\text{C}$		60		mJ
$R_{th(j-c)}$	per diode				0.11	K/W
Module						
L_{CE}				20		nH
$R_{CC'+EE'}$	res., terminal-chip	$T_C = 25^\circ\text{C}$		0.7		m Ω
		$T_C = 125^\circ\text{C}$		1		m Ω
$R_{th(c-s)}$	per module			0.04		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t		to terminals (M6)	2.5		5	Nm
						Nm
w					300	g
Temperature Sensor						
R_{100}	$T_C=100^\circ\text{C}$ ($R_{25}=5\text{ k}\Omega$)			$493 \pm 5\%$		Ω
$B_{100/125}$	$R_{(T)}=R_{100}\exp[B_{100/125}(1/T-1/T_{100})]$; $T[K]$;			$3550 \pm 2\%$		K



GB

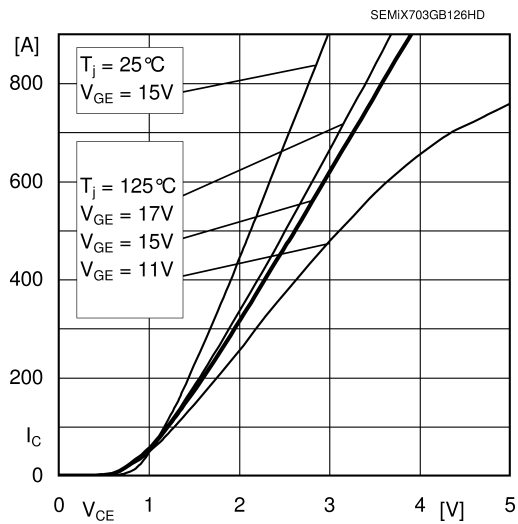


Fig. 1: Typ. output characteristic, inclusive $R_{CC} + EE'$

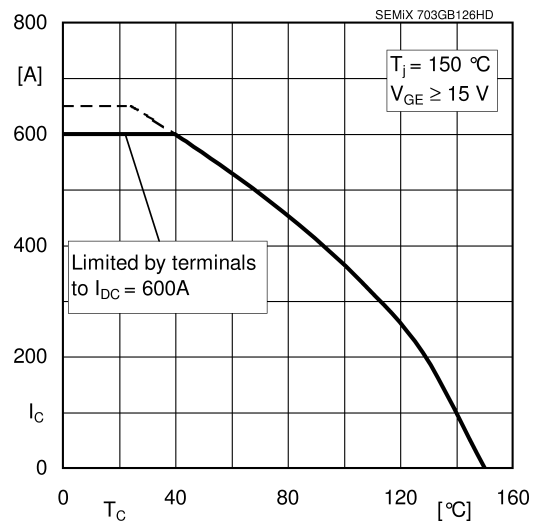


Fig. 2: Rated current vs. temperature $I_C = f(T_C)$

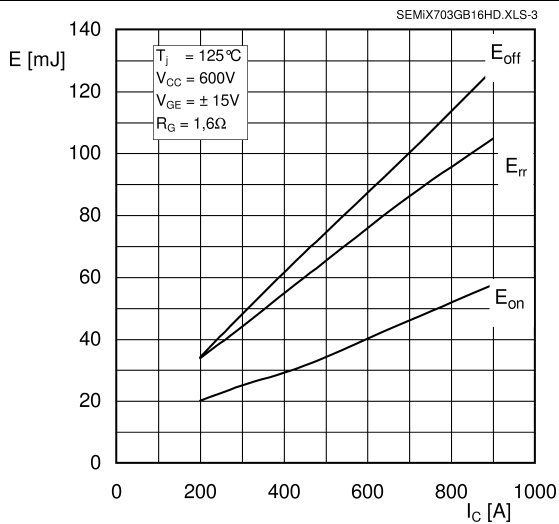


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

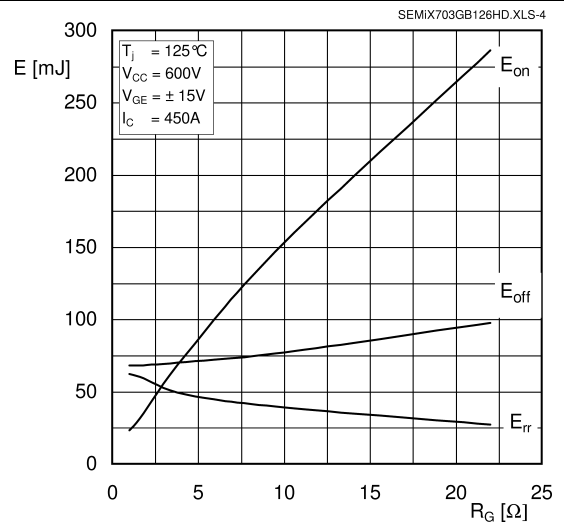


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

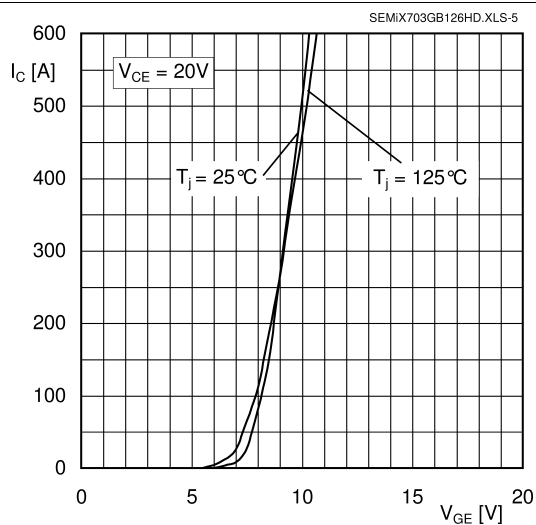


Fig. 5: Typ. transfer characteristic

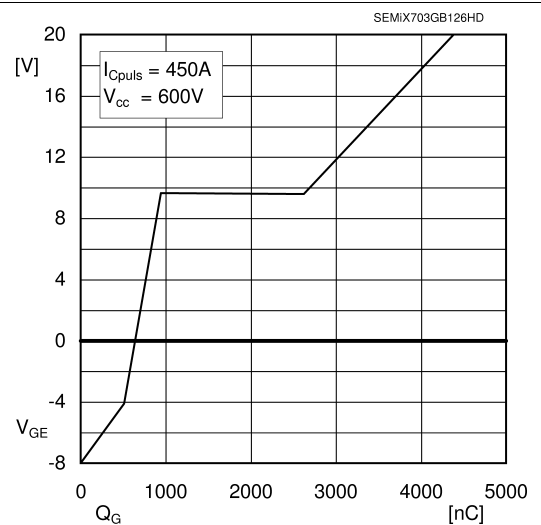
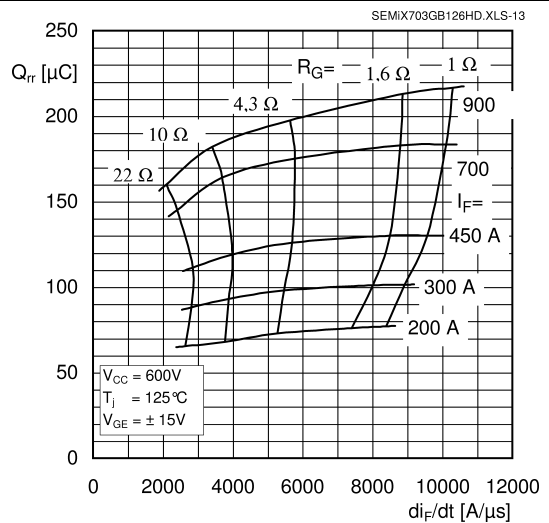
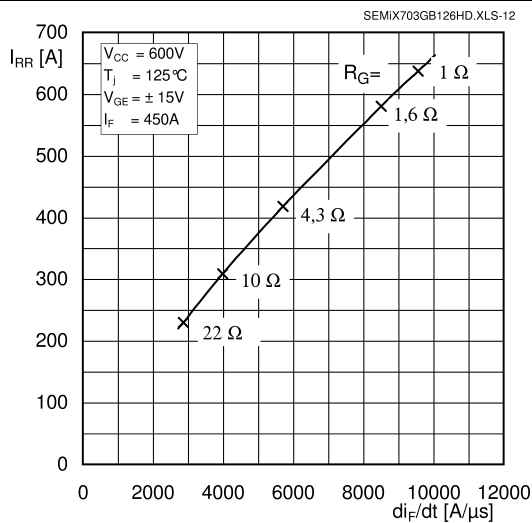
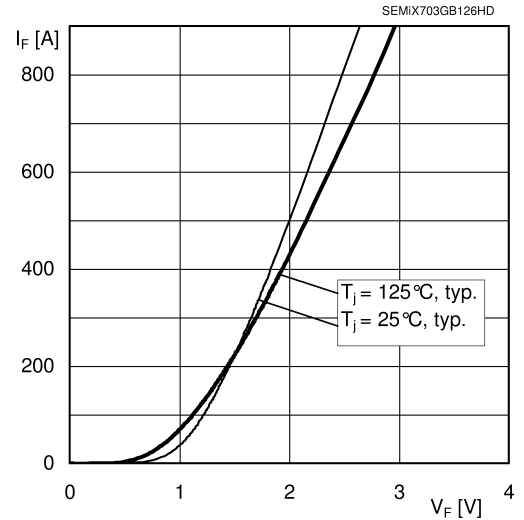
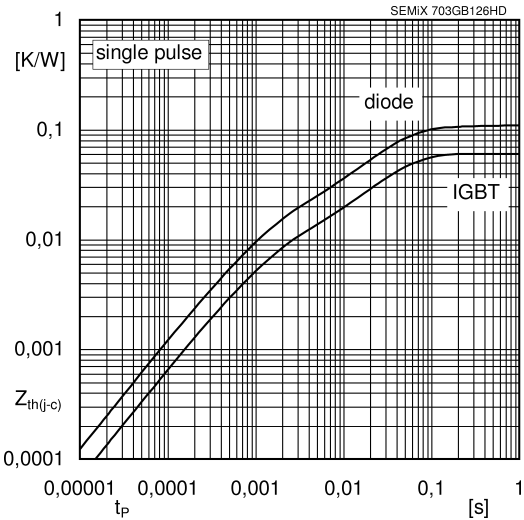
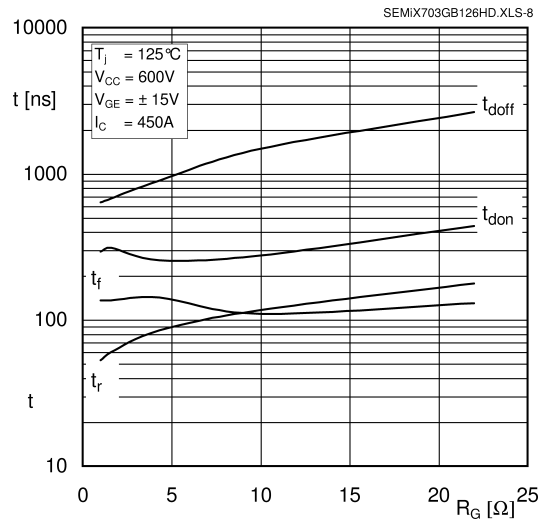
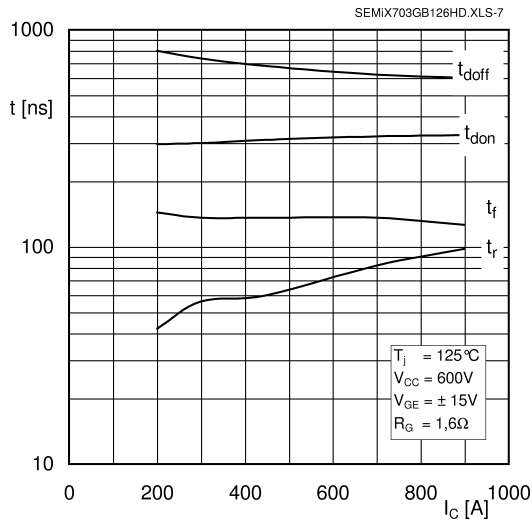


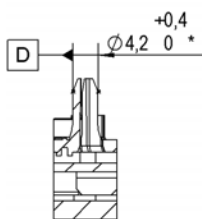
Fig. 6: Typ. gate charge characteristic



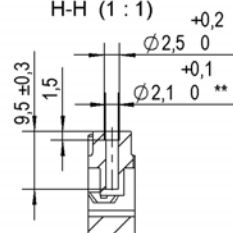
SEMiX703GB126HDs

Case: SEMiX 3s

guide pin left
F-F (1 : 1)



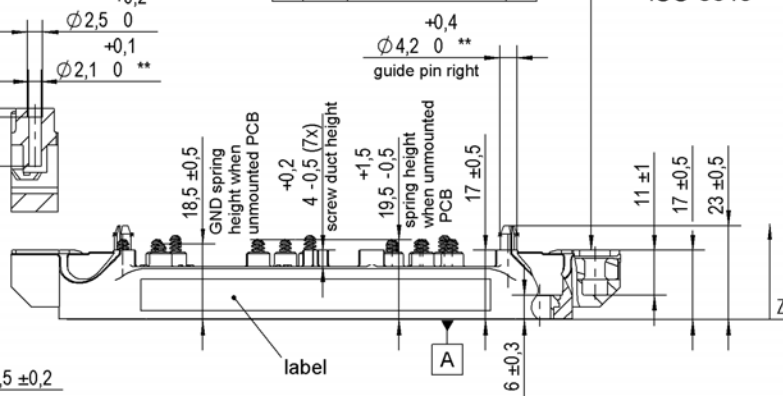
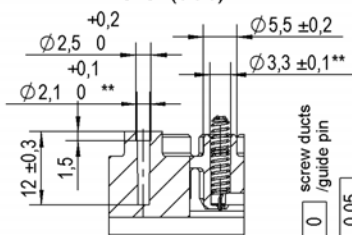
screw duct
(1x centre):
H-H (1 : 1)



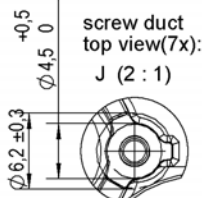
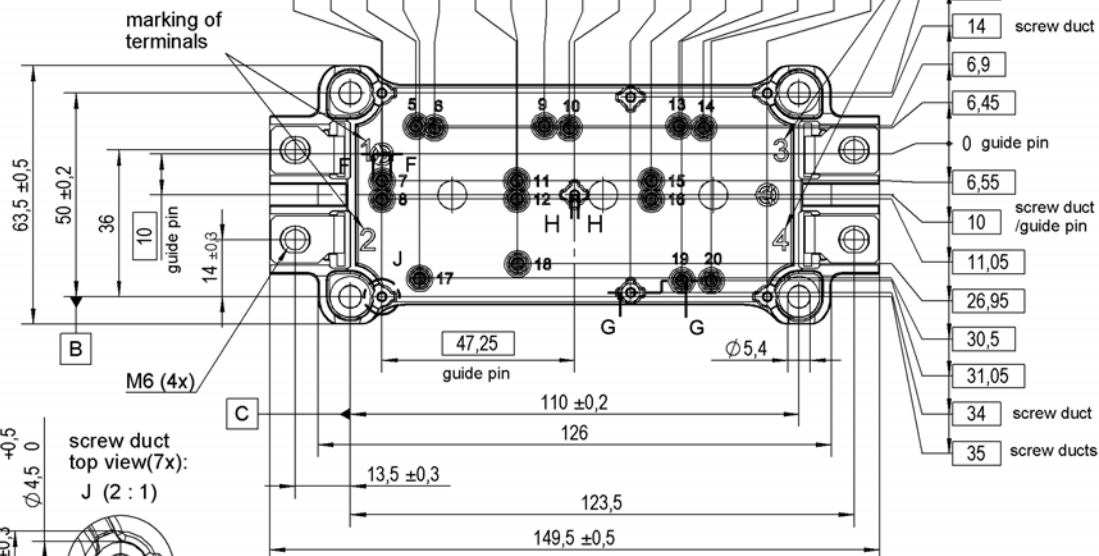
$\square$ 0,3	connector 1-2 / 3-4
$\parallel$ 0,2	each connector A

general tolerance:
ISO 2768-m
ISO 8015

screw duct (6x)
spring duct (16x):
G-G (1 : 1)



All measures in Z-direction
valid when mounted to heat sink



*guide pin left with

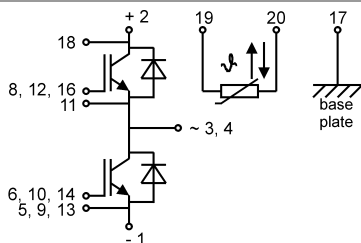
$\oplus$ Ø 0,25	A	B	C
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**screw ducts / spring ducts / guide pin right with

$\oplus$ Ø 0,5	A	B	D
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Rules for the contact PCB:
- holes guidepins = $\phi 4 \pm 0,1$ / position tolerance $\pm 0,1$
- holes for screws = $\phi 3,3 \pm 0,1$ / position tolerance $\pm 0,1$
- spring contact pad = $\phi 3,6 \pm 0,1$ / position tolerance $\pm 0,1$

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spring configuration

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.